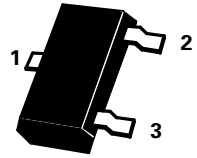
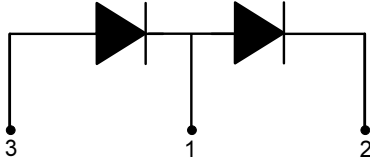


SOT23 SILICON PLANAR LOW LEAKAGE SERIES DIODE PAIR

ISSUE 2 – SEPTEMBER 1995 ♻

FLLD261

DIODE PIN CONNECTION



SOT23

PART MARKING DETAIL – P8A

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Average Rectified Forward Current	$I_{F(AV)}$	250	mA
Non-Repetitive Peak Forward Current (t=1μs)	I_{FSM}	3.0	A
Power Dissipation at $T_{amb} = 25^{\circ}\text{C}$	P_{tot}	330	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Reverse Current	I_R		5 5	nA μA	$V_{RRM}=100\text{V}$ $V_{RRM}=100\text{V}, T_{amb}=150^{\circ}\text{C}$
Reverse Recovery Time*	t_{rr}		400	ns	$I_F = I_R = 50 - 400\text{mA}$
Forward Recovery Time	t_{fr}		10	ns	$I_F = 10\text{mA}$
Diode Capacitance	C_d		4	pF	$V_R = 1\text{V}, f = 1\text{MHz}$
Forward Overshoot Voltage	V_{fr}		Typ 0.9	V	$I_F = 10\text{mA}$, Rise time = $5\text{ns} \pm 20\%$
Forward Voltage	V_F		1.4	V	$I_F = -200\text{mA}$

*Time for I_R to recover to 10% of I_R peak
For typical characteristics graphs see FLLD263 datasheet.

FLLD258
FLLD261
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TYPICAL CHARACTERISTICS

